

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1. (Previously Presented) A method of operating a transistor device comprising:  
floating a gate electrode of the transistor device;  
applying a voltage between a drain and a source electrode of the transistor device to cause a burned region in a channel region of the transistor device, even after the voltage is removed.
2. (Previously Presented) The method of claim 1 wherein the burned region provides a low impedance path between the drain and source electrodes.
3. (Previously Presented) The method of claim 1 wherein the burned region extends from the drain to the source and has a deeper depth closer to the drain than the source electrode.
4. (Previously Presented) The method of claim 1 wherein an impedance for the transistor device is about five times or greater than that for transistor device with the burned region.
- 5-11. (Canceled).
12. (Previously Presented) A method of operating an electronic system comprising programming one or more transistor devices according to the method recited in claim 1.
- 13-17. (Canceled).

18. (Previously Presented) The method of claim 1 wherein the transistor device has a width of 0.22 microns or less and a length of 0.13 microns or less.

19. (Previously Presented) The method of claim 1 wherein the transistor device is at least one of a MOSFET transistor, n-type MOSFET transistor, or p-type MOSFET transistor.

20. (Previously Presented) The method of claim 1 wherein the applying a voltage comprises:

applying a breakdown voltage to the drain electrode of the transistor device; and  
after applying the breakdown voltage, applying a burning voltage to the drain electrode of the transistor device, wherein the burning voltage is greater than the breakdown voltage.

21.-22. (Canceled).